


IN THE CLAIMS

Please cancel claims 1-~~15~~¹¹ without prejudice or disclaimer and add new claims ~~16-25~~¹²⁻²¹ as

follows:

 16. A gallium nitride semiconductor light emitting device having emission wavelengths within a band corresponding to ultraviolet to green, comprising a semiconductor substrate, an active layer having a quantum well structure and made of nitride semiconductor containing at least indium and gallium, and a first cladding layer and a second cladding layer for sandwiching the active layer therebetween, wherein

the active layer consists of two to four quantum well layers and one to three barrier layers each interposed between the quantum well layers, and the one or each barrier layer has a layer thickness of 4 nm or less.

13 17. The gallium nitride semiconductor light emitting device according to claim ~~16~~¹², wherein each of the quantum well layers has electrons and holes uniformly distributed therein.

14 18. The gallium nitride semiconductor light emitting device according to claim ~~16~~¹², wherein the gallium nitride semiconductor light emitting device is a semiconductor laser device and the active layer forms an oscillating section of the semiconductor laser device.

15 19. The gallium nitride semiconductor light emitting device according to claim ~~18~~¹⁴, wherein the semiconductor laser device is a self-oscillating semiconductor laser device.

16 20. The gallium nitride semiconductor light emitting device according to claim ~~18~~¹⁴, further comprising a driving circuit for injecting an electric current into the semiconductor laser device.

17 21. The gallium nitride semiconductor light emitting device according to claim ~~20~~¹⁶, wherein the electric current is a modulated current and a modulation frequency of the current is 300 MHz or more.

18 22. A gallium nitride semiconductor laser device having emission wavelengths within a band corresponding to ultraviolet to green, comprising a semiconductor substrate, an active layer

having a quantum well structure and made of nitride semiconductor containing at least indium and gallium, and a first cladding layer and a second cladding layer for sandwiching the active layer therebetween, wherein

the active layer forms an oscillating section of the semiconductor laser device, and consists of two to four quantum well layers and one to three barrier layers each interposed between the quantum well layers, and the one or each barrier layer has a layer thickness of 4 nm or less, and wherein one of the first and second cladding layers is a p-type cladding layer, and the p-type cladding layer has a ridge portion and a planar portion on opposite sides of the ridge portion.

¹⁹ 23. The gallium nitride semiconductor laser device according to claim ¹⁸ 22, wherein the ridge has a width of about 1 μm to 5 μm .

²⁰ 24. The gallium nitride semiconductor laser device according to claim ¹⁸ 22, wherein said planar portion has a film thickness of 0.05 μm to 0.5 μm .

²¹ 25. The gallium nitride semiconductor light emitting device according to claim ¹⁴ 18, wherein said light emitting device generates a modulated optical output when an electric current is injected thereinto.